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## Solvothermal Co-Reduction Route to Nanocrystalline

## III-V Semiconductor InAs

## Supporting Information:

Fig.1 XRD pattern of the sample prepared at 300 °C shows a perfectly crystallized sample with average size about 15nm.(Calculated by Scherer Formula)

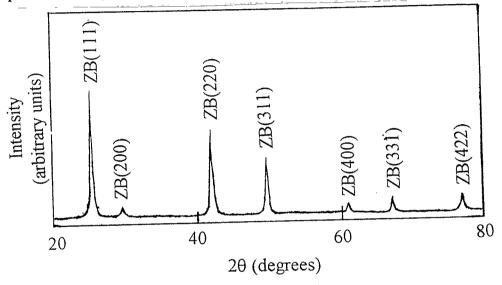


Fig. 2 TEM image and Electron Diffraction Pattern of the sample prepared at 300 °C. In the TEM image, the particles can be clearly distinguished from each other, with uniform sizes of 15nm or so. The Electron Diffraction pattern shows a well crystallized polycrystalline sample.

